BAS19L, BAS20L, BAS21L, BAS21DW5

High Voltage Switching Diode

ON Semiconductor®

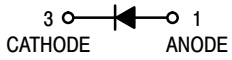
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HIGH VOLTAGE SWITCHING DIODE

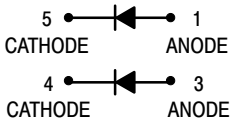
Features

- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant
- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable

SOT−23



SC−88A



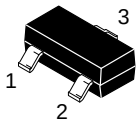
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage BAS19 BAS20 BAS21	V_R	 120 200 250	Vdc
Repetitive Peak Reverse Voltage BAS19 BAS20 BAS21	V_{RRM}	 120 200 250	Vdc
Continuous Forward Current	I_F	200	mAdc
Peak Forward Surge Current (1/2 Cycle, Sine Wave, 60 Hz)	I_{FSM}	2	A
Repetitive Peak Forward Current (Pulse Train: T_{ON} = 1 s, T_{OFF} = 0.5 s)	I_{FRM}	0.6	A
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C
Power Dissipation (Note 1)	P_D	385	mW
Electrostatic Discharge	ESD	HM < 500 MM < 400	V V

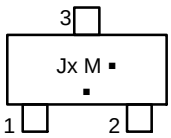
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted on FR−5 Board = 1.0 x 0.75 x 0.062 in.

MARKING DIAGRAMS

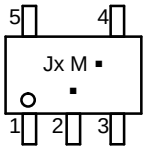


SOT−23 (TO−236)
CASE 318
STYLE 8





SC−88A (SOT−353)
CASE 419A



x = P, R, or S
P = BAS19L
R = BAS20L
S = BAS21L or BAS21DW5
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon the manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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THERMAL CHARACTERISTICS (SOT−23)

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 2) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction−to−Ambient (SOT−23)	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 3) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS (SC−88A)

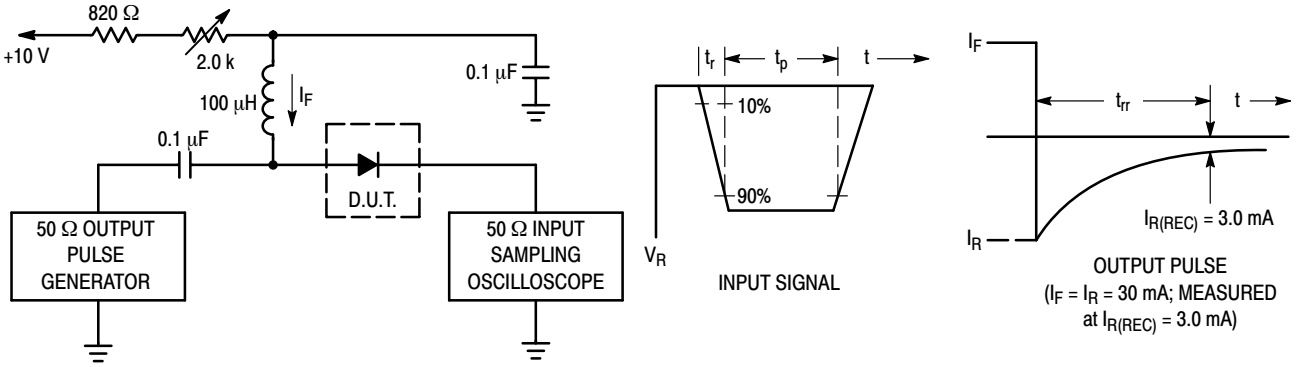
Characteristic	Symbol	Max	Unit
Power Dissipation (Note 4)	P_D	385	mW
Thermal Resistance − Junction−to−Ambient Derate Above 25°C	$R_{\theta JA}$	328 3.0	°C/W mW/°C
Maximum Junction Temperature	T_{Jmax}	150	°C
Operating Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

2. FR−5 = 1.0 × 0.75 × 0.062 in.
3. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.
4. Mounted on FR−5 Board = 1.0 x 0.75 x 0.062 in.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
Reverse Voltage Leakage Current		I_R			μAdc
(V_R = 100 Vdc)	BAS19		−	0.1	
(V_R = 150 Vdc)	BAS20		−	0.1	
(V_R = 200 Vdc)	BAS21		−	0.1	
(V_R = 100 Vdc, T_J = 150°C)	BAS19		−	100	
(V_R = 150 Vdc, T_J = 150°C)	BAS20		−	100	
(V_R = 200 Vdc, T_J = 150°C)	BAS21		−	100	
Reverse Breakdown Voltage		$V_{(BR)}$			Vdc
(I_{BR} = 100 μAdc)	BAS19		120	−	
(I_{BR} = 100 μAdc)	BAS20		200	−	
(I_{BR} = 100 μAdc)	BAS21		250	−	
Forward Voltage		V_F			Vdc
(I_F = 100 mAdc)			−	1.0	
(I_F = 200 mAdc)			−	1.25	
Diode Capacitance (V_R = 0, f = 1.0 MHz)		C_D	−	5.0	pF
Reverse Recovery Time (I_F = I_R = 30 mAdc, $I_{R(REC)}$ = 3.0 mAdc, R_L = 100)		t_{rr}	−	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

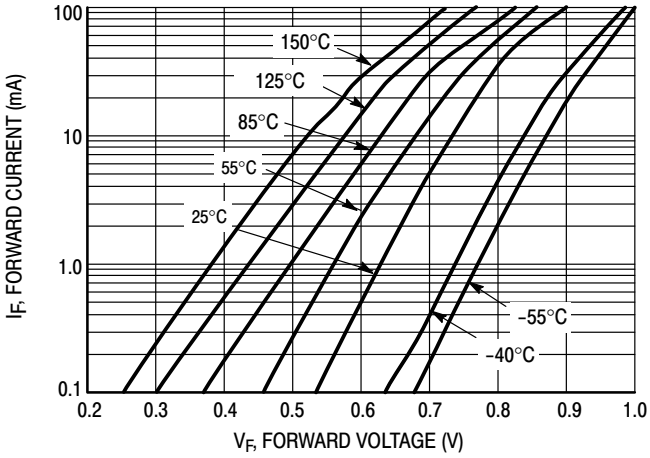


Figure 2. V_F vs. I_F

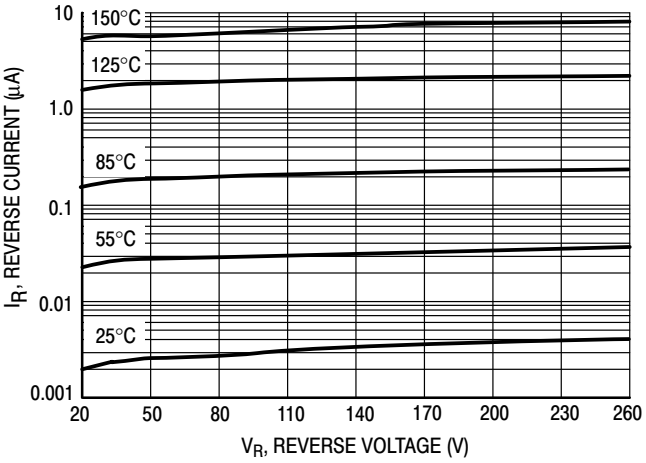


Figure 3. I_R vs. V_R

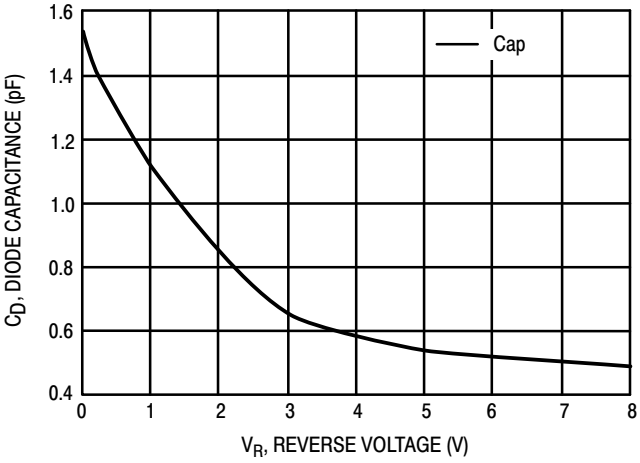


Figure 4. Capacitance

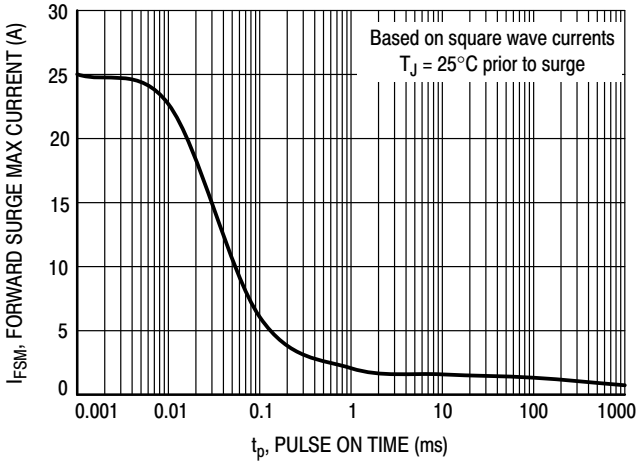


Figure 5. Forward Surge Current

ORDERING INFORMATION

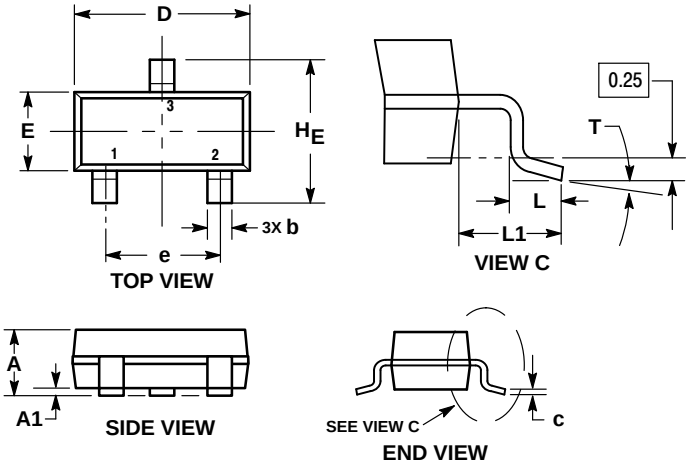
Device	Package	Shipping†
BAS19LT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
BAS19LT3G	SOT−23 (Pb−Free)	10000 / Tape & Reel
NSVBAS19LT1G*	SOT−23 (Pb−Free)	3000 / Tape & Reel
BAS20LT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
BAS20LT3G	SOT−23 (Pb−Free)	10000 / Tape & Reel
NSVBAS20LT3G*	SOT−23 (Pb−Free)	10000 / Tape & Reel
SBAS20LT1G*	SOT−23 (Pb−Free)	3000 / Tape & Reel
BAS21LT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
SBAS21LT1G*	SOT−23 (Pb−Free)	3000 / Tape & Reel
BAS21LT3G	SOT−23 (Pb−Free)	10000 / Tape & Reel
SBAS21LT3G*	SOT−23 (Pb−Free)	10000 / Tape & Reel
BAS21DW5T1G	SC−88A (Pb−Free)	3000 / Tape & Reel
SBAS21DW5T1G*	SC−88A (Pb−Free)	3000 / Tape & Reel
SBAS21DW5T3G*	SC−88A (Pb−Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AR

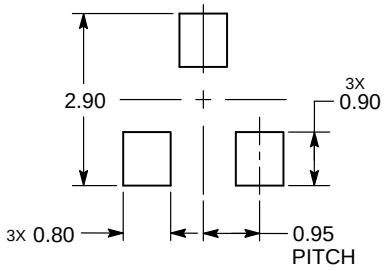


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

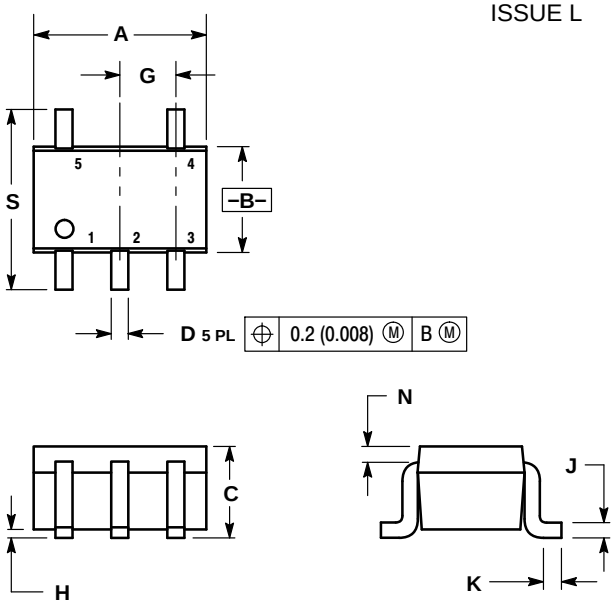
RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

PACKAGE DIMENSIONS

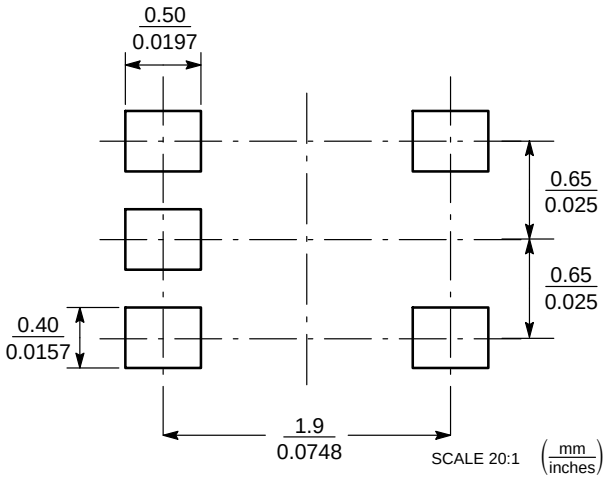
SC−88A (SC−70−5/SOT−353)
CASE 419A−02
ISSUE L



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

SOLDER FOOTPRINT



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